



FORM PTO-1449 (Modified) PATENT & TRADEMARK OFFICE LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	ATTY. DOCKET NO.: V00777/117	SERIAL NO.: 09/602,059
	APPLICANT: Charles McKenna et al	
	FILING DATE: June 23, 2000	GROUP: 2881

## U.S. PATENT DOCUMENTS

Exam Init	Ref Des	Document No.	Date	Name	Class	Sub Class	FILING DATE If Appropriate
U.M.E.		4,276,477	6/81	Enge	250	398	
U.M.E.		4,283,631	8/81	Turner	250	492B	
U.M.E.		4,899,059	2/90	Freytsis et al	250	492.2	
U.M.E.		4,922,106	5/90	Berrian et al	250	492.2	
U.M.E.		5,350,926	9/94	White et al	250	492.21	
U.M.E.		3,908,183	9/75	Ennis, Jr.	357	65	
U.M.E.		4,011,449	3/77	Ko et al	250	492.21	
U.M.E.		5,126,575	6/92	White	250	492.3	
U.M.E.		5,343,047	8/94	Ono et al	250	251	
U.M.E.		5,393,985	2/95	Yamakage et al	250	492.21	
U.M.E.		5,399,871	3/95	Ito et al	250	251	
U.M.E.		5,747,936	5/98	Harrison et al	250	492.21	
U.M.E.		5,767,522	6/98	Kodama	250	398	
U.M.E.		5,932,882	8/99	England et al	250	492.21	
U.M.E.		5,969,366	10/99	England et al	250	492.21	
U.M.E.		5,177,366	1/93	King et al	250	492.2	
U.M.E.		5,091,655	2/92	Dykstra	250	492.2	

## FOREIGN PATENT DOCUMENTS

	Country & Doc. No. (11)	Pub. Date (43)	Class	Sub Class	Translation Yes No
U.M.E.	EP 0 451 907	10/91			
U.M.E.	EP 0 685 872	12/95			

## OTHER ART

(Including Author, Title, Date, Pertinent Pages, Publication, Etc.)

U.M.E.		S.N. Hong et al, "Formation of Ultrashallow P+ -n Junctions by Low-Energy Boron Implantation Using a Modified Ion Implanter," Appl. Phys. Lett. 53(18), 31 Oct. 1988, pp. 1741-1743.
U.M.E.		A. Kluge et al, "A Flexible Target Chamber for a Varian 350 DF Implanter," Nuclear Inst. & Methods in Physics Research B37/38 (1989) pp. 584-587.
U.M.E.		T. Kawai et al, "Nissin EXCEED 2000 - A New High Performance Medium Current Implanter", Ion Implantation Tech. 94, S. Coffa et al (eds.), 1995 Elsevier Science Publ. B.V., pp. 470-473.
U.M.E.		H. Glavish et al, "Fast Magnetic Scanning and Ion Optical Features of the New Ibis Oxygen Implanter", Ion Implantation Tech., D.F. Downey et al (eds.), 1993 Elsevier Science Publ. B.V., pp. 397-400.
U.M.E.		A. Ray et al, "Overview of the Eaton NV-8200p High Beam Purity, Parallel Scanning Implanter", Ion Implantation Technology - 92, D. F. Downey et al (eds.), 1993 Elsevier Science Publ. B. V., pp. 401-404.

EXAMINER U.M.E. El-Shammaa	DATE CONSIDERED 10.31.02
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.